

DDR2 SDRAM UDIMM

MT18HTF25672AZ – 2GB

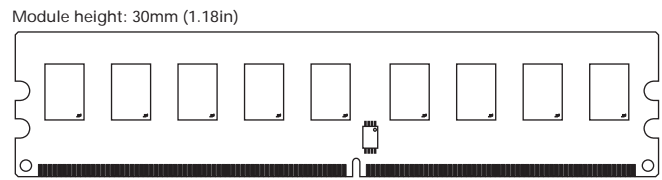
MT18HTF51272AZ – 4GB

For component data sheets, refer to Micron's Web site: www.micron.com

Features

- 240-pin, unbuffered dual in-line memory module
- Fast data transfer rates: PC2-3200, PC2-4200, PC2-5300, PC2-6400, or PC2-8500
- 2GB (256 Meg x 72), 4GB (512 Meg x 72)
- $V_{DD} = V_{DDQ} = +1.8V$
- $V_{DDSPD} = +1.7V$ to $+3.6V$
- JEDEC-standard 1.8V I/O (SSTL_18-compatible)
- Differential data strobe (DQS, DQS#) option
- 4n-bit prefetch architecture
- Supports ECC error detection and correction
- Dual rank
- Multiple internal device banks for concurrent operation
- Programmable CAS latency (CL)
- Posted CAS additive latency (AL)
- WRITE latency = READ latency - 1 tCK
- Programmable burst lengths (BL): 4 or 8
- Adjustable data-output drive strength
- 64ms, 8192-cycle refresh
- On-die termination (ODT)
- Serial presence-detect (SPD) with EEPROM
- Gold edge contacts
- Halogen-free

Figure 1: 240-Pin UDIMM (MO-237 R/C G)



Options

- Operating temperature¹
 - Commercial ($0^{\circ}C \leq T_C \leq +85^{\circ}C$)
- Package
 - 240-pin DIMM (halogen-free)
- Frequency/CAS latency
 - 1.875ns @ CL = 7 (DDR2-1066)
 - 2.5ns @ CL = 5 (DDR2-800)
 - 2.5ns @ CL = 6 (DDR2-800)
 - 3.0ns @ CL = 5 (DDR2-667)

Marking

None
Z
-1GA
-80E
-800
-667

1. Contact Micron for industrial temperature module offerings.

Table 1: Key Timing Parameters

Speed Grade	Industry Nomenclature	Data Rate (MT/s)					t _{RCD} (ns)	t _{RP} (ns)	t _{RC} (ns)
		CL = 7	CL = 6	CL = 5	CL = 4	CL = 3			
-1GA	PC2-8500	1066	800	667	533	400	13.125	13.125	58.125
-80E	PC2-6400	–	800	800	533	400	12.5	12.5	57.5
-800	PC2-6400	–	800	667	533	400	15	15	60
-667	PC2-5300	–	–	667	533	400	15	15	60
-53E	PC2-4200	–	–	–	533	400	15	15	60
-40E	PC2-3200	–	–	–	400	400	15	15	55

Table 2: Addressing

	2GB	4GB
Refresh count	8K	8K
Row address	16K A[13:0]	32K A[14:0]
Device bank address	8 BA[2:0]	8 BA[2:0]
Device page size per bank	1KB	1KB
Device configuration	1Gb (128 Meg x 8)	2Gb (256 Meg x 8)
Column address	1K A[9:0]	1K A[9:0]
Module rank address	2 S#[1:0]	2 S#[1:0]

Table 3: Part Numbers and Timing Parameters – 2GB Modules

Base device: MT47H128M8², 1Gb DDR2 SDRAM

Part Number ¹	Module Density	Configuration	Module Bandwidth	Memory Clock/ Data Rate	Latency (CL ⁻¹ -RCD ⁻¹ -RP)
MT18HTF25672AZ-1GA__	2GB	256 Meg x 72	8.5 GB/s	1.875ns/1066 MT/s	7-7-7
MT18HTF25672AZ-80E__	2GB	256 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	5-5-5
MT18HTF25672AZ-800__	2GB	256 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	6-6-6
MT18HTF25672AZ-667__	2GB	256 Meg x 72	5.3 GB/s	3.0ns/667 MT/s	5-5-5

Table 4: Part Numbers and Timing Parameters – 4GB Modules

Base device: MT47H256M8², 2Gb DDR2 SDRAM

Part Number ¹	Module Density	Configuration	Module Bandwidth	Memory Clock/ Data Rate	Latency (CL ⁻¹ -RCD ⁻¹ -RP)
MT18HTF51272AZ-80E__	4GB	512 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	5-5-5
MT18HTF51272AZ-800__	4GB	512 Meg x 72	6.4 GB/s	2.5ns/800 MT/s	6-6-6
MT18HTF51272AZ-667__	4GB	512 Meg x 72	5.3 GB/s	3.0ns/667 MT/s	5-5-5

- Notes: 1. All part numbers end with a two-place code (not shown) that designating component and PCB revisions. Consult factory for current revision codes. Example: MT18HTF25672AZ-667H1.
2. For component data sheets, refer to Micron's Web site.

Pin Assignments and Descriptions

Table 5: Pin Assignments

240-Pin UDIMM Front								240-Pin UDIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol		
1	V _{REF}	31	DQ19	61	A4	91	V _{SS}	121	V _{SS}	151	V _{SS}	181	V _{DDQ}	211	DM5
2	V _{SS}	32	V _{SS}	62	V _{DDQ}	92	DQS5#	122	DQ4	152	DQ28	182	A3	212	NC
3	DQ0	33	DQ24	63	A2	93	DQS5	123	DQ5	153	DQ29	183	A1	213	V _{SS}
4	DQ1	34	DQ25	64	V _{DD}	94	V _{SS}	124	V _{SS}	154	V _{SS}	184	V _{DD}	214	DQ46
5	V _{SS}	35	V _{SS}	65	V _{SS}	95	DQ42	125	DM0	155	DM3	185	CK0	215	DQ47
6	DQS0#	36	DQS3#	66	V _{SS}	96	DQ43	126	NC	156	NC	186	CK0#	216	V _{SS}
7	DQS0	37	DQS3	67	V _{DD}	97	V _{SS}	127	V _{SS}	157	V _{SS}	187	V _{DD}	217	DQ52
8	V _{SS}	38	V _{SS}	68	NC	98	DQ48	128	DQ6	158	DQ30	188	A0	218	DQ53
9	DQ2	39	DQ26	69	V _{DD}	99	DQ49	129	DQ7	159	DQ31	189	V _{DD}	219	V _{SS}
10	DQ3	40	DQ27	70	A10	100	V _{SS}	130	V _{SS}	160	V _{SS}	190	BA1	220	CK2
11	V _{SS}	41	V _{SS}	71	BA0	101	SA2	131	DQ12	161	CB4	191	V _{DDQ}	221	CK2#
12	DQ8	42	CB0	72	V _{DDQ}	102	NC	132	DQ13	162	CB5	192	RAS#	222	V _{SS}
13	DQ9	43	CB1	73	WE#	103	V _{SS}	133	V _{SS}	163	V _{SS}	193	SO#	223	DM6
14	V _{SS}	44	V _{SS}	74	CAS#	104	DQS6#	134	DM1	164	DM8	194	V _{DDQ}	224	NC
15	DQS1#	45	DQS8#	75	V _{DDQ}	105	DQS6	135	NC	165	NC	195	ODT0	225	V _{SS}
16	DQS1	46	DQS8	76	S1#	106	V _{SS}	136	V _{SS}	166	V _{SS}	196	A13	226	DQ54
17	V _{SS}	47	V _{SS}	77	ODT1	107	DQ50	137	CK1	167	CB6	197	V _{DD}	227	DQ55
18	NC	48	CB2	78	V _{DDQ}	108	DQ51	138	CK1#	168	CB7	198	V _{SS}	228	V _{SS}
19	NC	49	CB3	79	V _{SS}	109	V _{SS}	139	V _{SS}	169	V _{SS}	199	DQ36	229	DQ60
20	V _{SS}	50	V _{SS}	80	DQ32	110	DQ56	140	DQ14	170	V _{DDQ}	200	DQ37	230	DQ61
21	DQ10	51	V _{DDQ}	81	DQ33	111	DQ57	141	DQ15	171	CKE1	201	V _{SS}	231	V _{SS}
22	DQ11	52	CKE0	82	V _{SS}	112	V _{SS}	142	V _{SS}	172	V _{DD}	202	DM4	232	DM7
23	V _{SS}	53	V _{DD}	83	DQS4#	113	DQS7#	143	DQ20	173	NC	203	NC	233	NC
24	DQ16	54	BA2	84	DQS4	114	DQS7	144	DQ21	174 ¹	NC/A14	204	V _{SS}	234	V _{SS}
25	DQ17	55	NC	85	V _{SS}	115	V _{SS}	145	V _{SS}	175	V _{DDQ}	205	DQ38	235	DQ62
26	V _{SS}	56	V _{DDQ}	86	DQ34	116	DQ58	146	DM2	176	A12	206	DQ39	236	DQ63
27	DQS2#	57	A11	87	DQ35	117	DQ59	147	NC	177	A9	207	V _{SS}	237	V _{SS}
28	DQS2	58	A7	88	V _{SS}	118	V _{SS}	148	V _{SS}	178	V _{DD}	208	DQ44	238	V _{DDSPD}
29	V _{SS}	59	V _{DD}	89	DQ40	119	SDA	149	DQ22	179	A8	209	DQ45	239	SA0
30	DQ18	60	A5	90	DQ41	120	SCL	150	DQ23	180	A6	210	V _{SS}	240	SA1

Notes: 1. Pin 174 is NC for 2GB, or A14 for 4GB

Table 6: Pin Descriptions

Symbol	Type	Description
A[14:0]	Input (SSTL_18)	Address inputs: Provide the row address for ACTIVE commands, and the column address and auto precharge bit (A10) for READ/WRITE commands, to select one location out of the memory array in the respective bank. A10 sampled during a PRECHARGE command determines whether the PRECHARGE applies to one device bank (A10 LOW, device bank selected by BA[2/1:0]) or all device banks (A10 HIGH). The address inputs also provide the op-code during a LOAD MODE command. A[13:0] (2GB) and A[14:0] (4GB).
BA[2:0]	Input (SSTL_18)	Bank address inputs: BA[2/1:0] define to which device bank an ACTIVE, READ, WRITE, or PRECHARGE command is being applied. BA[2/1:0] define which mode register (MR, EMR1, EMR2, and EMR3) is loaded during the LOAD MODE command.
CK[2:0] CK#[2:0]	Input (SSTL_18)	Clock: CK and CK# are differential clock inputs. All control, command, and address input signals are sampled on the crossing of the positive edge of CK and the negative edge of CK#.
CKE[1:0]	Input (SSTL_18)	Clock enable: CKE enables (registered HIGH) and disables (registered LOW) internal circuitry and clocks on the DDR2 SDRAM.
DM[8:0]	Input (SSTL_18)	Input data mask: DM is an input mask signal for write data. Input data is masked when DM is sampled HIGH, along with the input data, during a write access. DM is sampled on both edges of DQS. Although the DM pins are input-only, DM loading is designed to match that of the DQ and DQS pins.
ODT[1:0]	Input (SSTL_18)	On-die termination: ODT enables (registered HIGH) and disables (registered LOW) termination resistance internal to the DDR2 SDRAM. When enabled in normal operation, ODT is only applied to the following pins: DQ, DQS, DQS#, DM, and CB. The ODT input will be ignored if disabled via the LOAD MODE command.
RAS#, CAS#, WE#	Input (SSTL_18)	Command inputs: RAS#, CAS#, and WE# (along with S#) define the command being entered.
S#[1:0]	Input (SSTL_18)	Chip select: S# enables (registered LOW) and disables (registered HIGH) the command decoder.
SA[2:0]	Input	Serial address inputs: These pins are used to configure the SPD EEPROM address range on the I ² C bus.
SCL	Input	Serial clock for SPD EEPROM: SCL is used to synchronize communication to and from the SPD EEPROM.
CB[7:0]	I/O (SSTL_18)	Check bits.
DQ[63:0]	I/O (SSTL_18)	Data input/output: Bidirectional data bus.
DQS[8:0], DQS#[8:0]	I/O (SSTL_18)	Data strobe: Output with read data. Edge-aligned with read data. Input with write data. Center-aligned with write data. DQS# is only used when differential data strobe mode is enabled via the LOAD MODE command.
SDA	I/O	Serial data: SDA is a bidirectional pin used to transfer addresses and data into and out of the SPD EEPROM on the module on the I ² C bus.
V _{DD} /V _{DDQ}	Supply	Power supply: 1.8V ±0.1V. The component V _{DD} and V _{DDQ} are connected to the module V _{DD} .
V _{DDSPD}	Supply	SPD EEPROM power supply: +1.7V to +3.6V.
V _{REF}	Supply	Reference voltage: V _{DD} /2.
V _{SS}	Supply	Ground.
NC	-	No connect: These pins are not connected on the module.



2GB, 4GB (x72, DR, ECC) 240-Pin DDR2 SDRAM UDIMM Pin Assignments and Descriptions

Table 7: Component DQ to Module Pin Map, Front

Component Number	Component DQ	Module DQ	Module Pin Number	Component Number	Component DQ	Module DQ	Module Pin Number
U1	0	4	122	U2	0	12	131
	1	3	10		1	11	22
	2	5	123		2	13	132
	3	2	9		3	10	21
	4	7	129		4	15	141
	5	0	3		5	8	12
	6	6	128		6	14	140
	7	1	4		7	9	13
U3	0	20	143	U4	0	28	152
	1	19	31		1	27	40
	2	21	144		2	29	153
	3	18	30		3	26	39
	4	23	150		4	31	159
	5	16	24		5	24	33
	6	22	149		6	30	158
	7	17	25		7	25	34
U5	0	CB4	161	U6	0	36	199
	1	CB3	49		1	35	87
	2	CB5	162		2	37	200
	3	CB2	48		3	34	86
	4	CB7	168		4	39	206
	5	CB0	42		5	32	80
	6	CB6	167		6	38	205
	7	CB1	43		7	33	81
U7	0	44	208	U8	0	52	217
	1	43	96		1	51	108
	2	45	209		2	53	218
	3	42	95		3	50	107
	4	47	215		4	55	227
	5	40	89		5	48	98
	6	46	214		6	54	226
	7	41	90		7	49	99
U9	0	60	229				
	1	59	117				
	2	61	230				
	3	58	116				
	4	63	236				
	5	56	110				
	6	62	235				
	7	57	111				

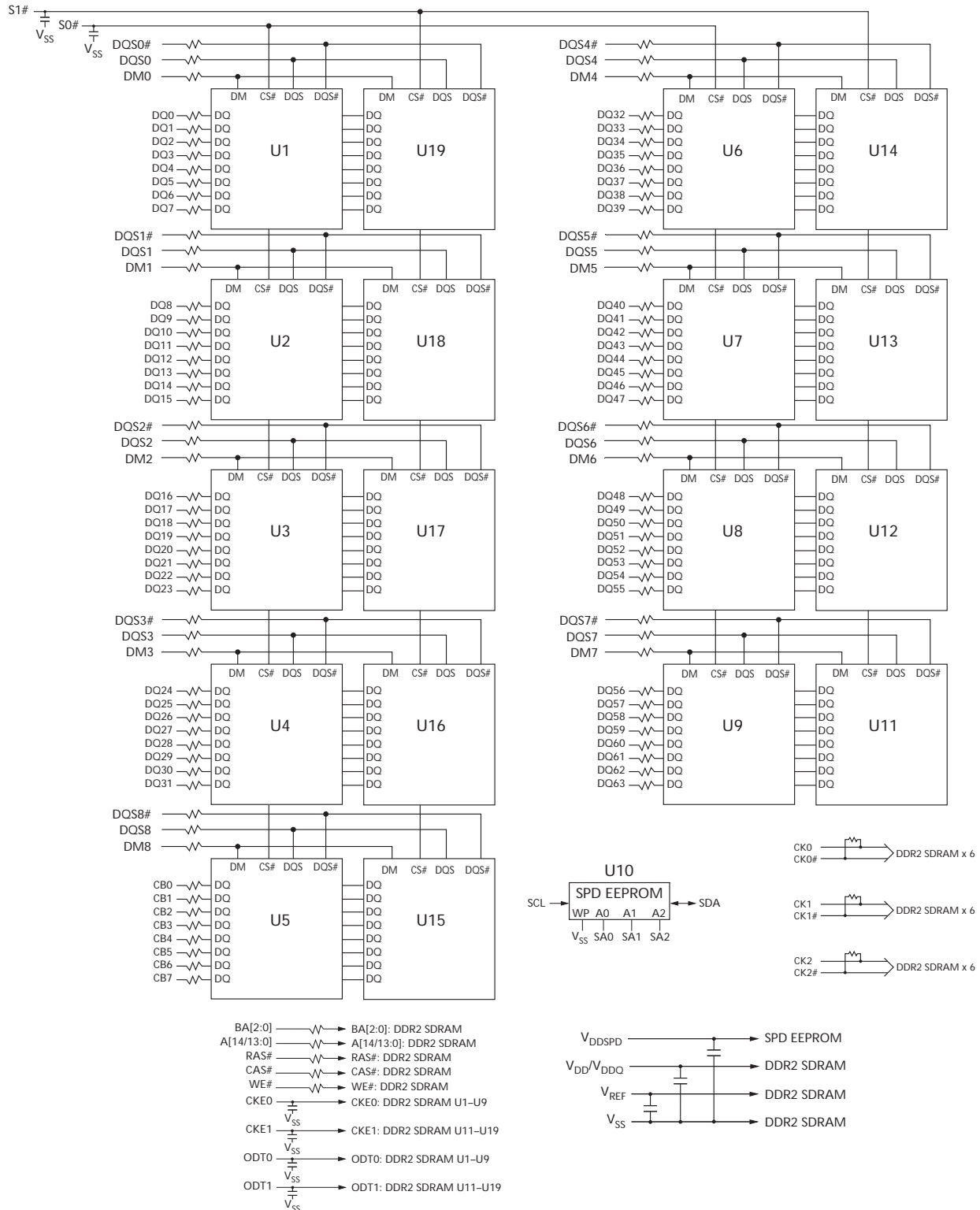


Table 8: Component DQ to Module Pin Map, Back

Component Number	Component DQ	Module DQ	Module Pin Number	Component Number	Component DQ	Module DQ	Module Pin Number
U11	0	59	117	U12	0	51	108
	1	60	229		1	52	217
	2	58	116		2	50	107
	3	61	230		3	53	218
	4	56	110		4	48	98
	5	63	236		5	55	227
	6	57	111		6	49	99
	7	62	235		7	54	226
U13	0	43	96	U14	0	35	87
	1	44	208		1	36	199
	2	42	95		2	34	86
	3	45	209		3	37	200
	4	40	89		4	32	80
	5	47	215		5	39	206
	6	41	90		6	33	81
	7	46	214		7	38	205
U15	0	CB3	49	U16	0	27	40
	1	CB4	161		1	28	152
	2	CB2	48		2	26	39
	3	CB5	162		3	29	153
	4	CB0	42		4	24	33
	5	CB7	168		5	31	159
	6	CB1	43		6	25	34
	7	CB6	167		7	30	158
U17	0	19	31	U18	0	11	22
	1	20	143		1	12	131
	2	18	30		2	11	21
	3	21	144		3	13	132
	4	16	24		4	8	12
	5	23	150		5	15	141
	6	17	25		6	9	13
	7	22	149		7	14	140
U19	0	3	10				
	1	4	122				
	2	2	9				
	3	5	123				
	4	0	3				
	5	7	129				
	6	1	4				
	7	6	128				

Functional Block Diagram

Figure 2: Functional Block Diagram



General Description

The MT18HTF25672AZ and MT18HTF51272AZ DDR2 SDRAM modules are high-speed, CMOS, dynamic random-access 2GB and 4GB memory modules organized in x72 configurations. These DDR2 SDRAM modules use internally configured 8-bank (1Gb, 2Gb) DDR2 SDRAM devices.

DDR2 SDRAM modules use double data rate architecture to achieve high-speed operation. The double data rate architecture is essentially a $4n$ -prefetch architecture with an interface designed to transfer two data words per clock cycle at the I/O pins. A single read or write access for the DDR2 SDRAM module effectively consists of a single $4n$ -bit-wide, one-clock-cycle data transfer at the internal DRAM core and four corresponding n -bit-wide, one-half-clock-cycle data transfers at the I/O pins.

A bidirectional data strobe (DQS, DQS#) is transmitted externally, along with data, for use in data capture at the receiver. DQS is a strobe transmitted by the DDR2 SDRAM device during READs and by the memory controller during WRITEs. DQS is edge-aligned with data for READs and center-aligned with data for WRITEs.

DDR2 SDRAM modules operate from a differential clock (CK and CK#); the crossing of CK going HIGH and CK# going LOW will be referred to as the positive edge of CK. Commands (address and control signals) are registered at every positive edge of CK. Input data is registered on both edges of DQS, and output data is referenced to both edges of DQS, as well as to both edges of CK.

Serial Presence-Detect Operation

DDR2 SDRAM modules incorporate serial presence-detect. The SPD data is stored in a 256-byte EEPROM. The first 128 bytes are programmed by Micron to identify the module type and various SDRAM organizations and timing parameters. The remaining 128 bytes of storage are available for use by the customer. System READ/WRITE operations between the master (system logic) and the slave EEPROM device occur via a standard I²C bus using the DIMM's SCL (clock) and SDA (data) signals, together with SA[2:0], which provide eight unique DIMM/EEPROM addresses. Write protect (WP) is connected to Vss, permanently disabling hardware write protection.

Electrical Specifications

Stresses greater than those listed in Table 9 may cause permanent damage to the DRAM devices on the module. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in each device's data sheet is not implied. Exposure to absolute maximum rating conditions for extended periods may adversely affect reliability.

Table 9: Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Units	
V_{DD}/V_{DDQ}	V_{DD} supply voltage relative to V_{SS}	-0.5	+2.3	V	
V_{IN}, V_{OUT}	Voltage on any pin relative to V_{SS}	-0.5	+2.3	V	
I_I	Input leakage current; Any input $0V \leq V_{IN} \leq V_{DD}$; V_{REF} input $0V \leq V_{IN} \leq 0.95V$; (All other pins not under test = 0V)	Command/Address RAS#, CAS#, WE#, BA	-90	+90	μA
		S#, CKE, ODT	-45	+45	
		CK, CK#	-30	+30	
		DM	-10	+10	
I_{OZ}	Output leakage current; $0V \leq V_{OUT} \leq V_{DDQ}$; DQs and ODT are disabled	-10	+10	μA	
I_{VREF}	V_{REF} leakage current; V_{REF} = valid V_{REF} level	-36	+36	μA	
T_C^{-1}	DDR2 SDRAM device case operating temperature ²	0	+85	$^{\circ}C$	

- Notes: 1. The refresh rate is required to double when T_C exceeds $85^{\circ}C$
 2. For further information, refer to technical note TN-00-08: Thermal Applications, available on Micron's Web site.

DRAM Operating Conditions

Recommended AC operating conditions are given in the DDR2 component data sheets. Component specifications are available on Micron's Web site at www.micron.com. Module speed grades correlate with component speed grades, as shown in Table 10.

Table 10: Module and Component Speed Grades
DDR2 components may exceed the listed module speed grades

Module Speed Grade	Component Speed Grade
-1GA	-187E
-80E	-25E
-800	-25
-667	-3
-53E	-37E
-40E	-5E

Design Considerations

Simulations

Micron memory modules are designed to optimize signal integrity through carefully designed terminations, controlled board impedances, routing topologies, trace length matching, and decoupling. However, good signal integrity starts at the system level. Micron encourages designers to simulate the signal characteristics of the system's memory bus to ensure adequate signal integrity of the entire memory system.

Power

Operating voltages are specified at the DRAM, not at the edge connector of the module. Designers must account for any system voltage drops at anticipated power levels to ensure the required supply voltage is maintained.

Table 11: DDR2 IDD Specifications and Conditions – 2GB

Values shown for MT47H128M8 DDR2 SDRAM only and are computed from values specified in the 1Gb (128 Meg x 8) component data sheet

Parameter/Condition	Symbol	-1GA	-80E/ -800	-667	Units	
Operating one bank active-precharge current: $t_{CK} = t_{CK}(I_{DD})$, $t_{RC} = t_{RC}(I_{DD})$, $t_{RAS} = t_{RAS\ MIN}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD0}^1	976	776	736	mA	
Operating one bank active-read-precharge current: $I_{OUT} = 0mA$; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK}(I_{DD})$, $t_{RC} = t_{RC}(I_{DD})$, $t_{RAS} = t_{RAS\ MIN}(I_{DD})$, $t_{RCD} = t_{RCD}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data pattern is same as I_{DD4W}	I_{DD1}^1	1096	936	856	mA	
Precharge power-down current: All device banks idle; $t_{CK} = t_{CK}(I_{DD})$; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD2P}^2	112	112	112	mA	
Precharge quiet standby current: All device banks idle; $t_{CK} = t_{CK}(I_{DD})$; CKE is HIGH, S# is HIGH; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD2Q}^2	960	800	640	mA	
Precharge standby current: All device banks idle; $t_{CK} = t_{CK}(I_{DD})$; CKE is HIGH, S# is HIGH; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD2N}^2	960	800	640	mA	
Active power-down current: All device banks open; $t_{CK} = t_{CK}(I_{DD})$; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD3P}^2	Fast PDN exit MR[12] = 0	800	640	480	mA
		Slow PDN exit MR[12] = 1	160	160	160	mA
Active standby current: All device banks open; $t_{CK} = t_{CK}(I_{DD})$, $t_{RAS} = t_{RAS\ MAX}(I_{DD})$, $t_{RP} = t_{RP}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD3N}^2	1120	960	880	mA	
Operating burst write current: All device banks open; Continuous burst writes; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK}(I_{DD})$, $t_{RAS} = t_{RAS\ MAX}(I_{DD})$, $t_{RP} = t_{RP}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD4W}^1	1736	1336	1136	mA	
Operating burst read current: All device banks open; Continuous burst reads; $I_{OUT} = 0mA$; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK}(I_{DD})$, $t_{RAS} = t_{RAS\ MAX}(I_{DD})$, $t_{RP} = t_{RP}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD4R}^1	1736	1336	1136	mA	
Burst refresh current: $t_{CK} = t_{CK}(I_{DD})$; REFRESH command at every $t_{RFC}(I_{DD})$ interval; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD5}^2	4240	3760	3440	mA	
Self refresh current: CK and CK# at 0V; CKE $\leq 0.2V$; Other control and address bus inputs are floating; Data bus inputs are floating	I_{DD6}^2	112	112	112	mA	
Operating bank interleave read current: All device banks interleaving reads; $I_{OUT} = 0mA$; BL = 4, CL = CL (I_{DD}), AL = $t_{RCD}(I_{DD}) - 1 \times t_{CK}(I_{DD})$; $t_{CK} = t_{CK}(I_{DD})$, $t_{RC} = t_{RC}(I_{DD})$, $t_{RRD} = t_{RRD}(I_{DD})$, $t_{RCD} = t_{RCD}(I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are stable during DESELECTs; Data bus inputs are switching	I_{DD7}^1	3456	2736	2296	mA	

Notes: 1. Value calculated as one module rank in this operating condition and all other module ranks in I_{DD2P} (CKE LOW).

2. Value calculated reflects all module ranks in this operating condition.

Table 12: DDR2 IDD Specifications and Conditions – 4GB

Values shown for MT47H256M8 DDR2 SDRAM only and are computed from values specified in the 2Gb (256 Meg x 8) component data sheet

Parameter/Condition	Symbol	-80E/-800	-667	Units	
Operating one bank active-precharge current: $t_{CK} = t_{CK} (I_{DD})$, $t_{RC} = t_{RC} (I_{DD})$, $t_{RAS} = t_{RAS} \text{ MIN} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD0}^1	1000	880	mA	
Operating one bank active-read-precharge current: $I_{OUT} = 0\text{mA}$; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK} (I_{DD})$, $t_{RC} = t_{RC} (I_{DD})$, $t_{RAS} = t_{RAS} \text{ MIN} (I_{DD})$, $t_{RCD} = t_{RCD} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data pattern is same as I_{DD4W}	I_{DD1}^1	1400	1240	mA	
Precharge power-down current: All device banks idle; $t_{CK} = t_{CK} (I_{DD})$; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD2P}^2	160	160	mA	
Precharge quiet standby current: All device banks idle; $t_{CK} = t_{CK} (I_{DD})$; CKE is HIGH, S# is HIGH; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD2Q}^2	1040	880	mA	
Precharge standby current: All device banks idle; $t_{CK} = t_{CK} (I_{DD})$; CKE is HIGH, S# is HIGH; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD2N}^2	1120	960	mA	
Active power-down current: All device banks open; $t_{CK} = t_{CK} (I_{DD})$; CKE is LOW; Other control and address bus inputs are stable; Data bus inputs are floating	I_{DD3P}^2	Fast PDN exit MR[12] = 0	720	640	mA
		Slow PDN exit MR[12] = 1	224	224	mA
Active standby current: All device banks open; $t_{CK} = t_{CK} (I_{DD})$, $t_{RAS} = t_{RAS} \text{ MAX} (I_{DD})$, $t_{RP} = t_{RP} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD3N}^2	1040	880	mA	
Operating burst write current: All device banks open; Continuous burst writes; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK} (I_{DD})$, $t_{RAS} = t_{RAS} \text{ MAX} (I_{DD})$, $t_{RP} = t_{RP} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD4W}^1	1520	1280	mA	
Operating burst read current: All device banks open; Continuous burst reads; $I_{OUT} = 0\text{mA}$; BL = 4, CL = CL (I_{DD}), AL = 0; $t_{CK} = t_{CK} (I_{DD})$, $t_{RAS} = t_{RAS} \text{ MAX} (I_{DD})$, $t_{RP} = t_{RP} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are switching; Data bus inputs are switching	I_{DD4R}^1	1600	1440	mA	
Burst refresh current: $t_{CK} = t_{CK} (I_{DD})$; REFRESH command at every $t_{RFC} (I_{DD})$ interval; CKE is HIGH, S# is HIGH between valid commands; Other control and address bus inputs are switching; Data bus inputs are switching	I_{DD5}^2	4800	4480	mA	
Self refresh current: CK and CK# at 0V; CKE $\leq 0.2\text{V}$; Other control and address bus inputs are floating; Data bus inputs are floating	I_{DD6}^2	160	160	mA	
Operating bank interleave read current: All device banks interleaving reads; $I_{OUT} = 0\text{mA}$; BL = 4, CL = CL (I_{DD}), AL = $t_{RCD} (I_{DD}) - 1 \times t_{CK} (I_{DD})$; $t_{CK} = t_{CK} (I_{DD})$, $t_{RC} = t_{RC} (I_{DD})$, $t_{RRD} = t_{RRD} (I_{DD})$, $t_{RCD} = t_{RCD} (I_{DD})$; CKE is HIGH, S# is HIGH between valid commands; Address bus inputs are stable during DESELECTs; Data bus inputs are switching	I_{DD7}^1	3200	2800	mA	

- Notes: 1. Value calculated as one module rank in this operating condition and all other module ranks in I_{DD2P} (CKE LOW).
2. Value calculated reflects all module ranks in this operating condition.

Serial Presence-Detect

Table 13: Serial Presence-Detect EEPROM DC Operating Conditions

Parameter/Condition	Symbol	Min	Max	Units
Supply voltage	V_{DDSPD}	1.7	3.6	V
Input high voltage: Logic 1; All inputs	V_{IH}	$V_{DDSPD} \times 0.7$	$V_{DDSPD} + 0.5$	V
Input low voltage: Logic 0; All inputs	V_{IL}	-0.6	$V_{DDSPD} \times 0.3$	V
Output low voltage: $I_{OUT} = 3mA$	V_{OL}	-	0.4	V
Input leakage current: $V_{IN} = GND$ to V_{DD}	I_{LI}	0.10	3	μA
Output leakage current: $V_{OUT} = GND$ to V_{DD}	I_{LO}	0.05	3	μA
Standby current	I_{SB}	1.6	4	μA
Power supply current, READ: SCL clock frequency = 100 KHz	I_{CCR}	0.4	1	mA
Power supply current, WRITE: SCL clock frequency = 100 KHz	I_{CCW}	2	3	mA

Table 14: Serial Presence-Detect EEPROM AC Operating Conditions

Parameter/Condition	Symbol	Min	Max	Units	Notes
SCL LOW to SDA data-out valid	t_{AA}	0.2	0.9	μs	1
Time the bus must be free before a new transition can start	t_{BUF}	1.3	-	μs	
Data-out hold time	t_{DH}	200	-	ns	
SDA and SCL fall time	t_F	-	300	ns	2
Data-in hold time	$t_{HD:DAT}$	0	-	μs	
Start condition hold time	$t_{HD:STA}$	0.6	-	μs	
Clock HIGH period	t_{HIGH}	0.6	-	μs	
Noise suppression time constant at SCL, SDA inputs	t_I	-	50	ns	
Clock LOW period	t_{LOW}	1.3	-	μs	
SDA and SCL rise time	t_R	-	0.3	μs	2
SCL clock frequency	f_{SCL}	-	400	KHz	
Data-in setup time	$t_{SU:DAT}$	100	-	ns	
Start condition setup time	$t_{SU:STA}$	0.6	-	μs	3
Stop condition setup time	$t_{SU:STO}$	0.6	-	μs	
WRITE cycle time	t_{WRC}	-	10	ms	4

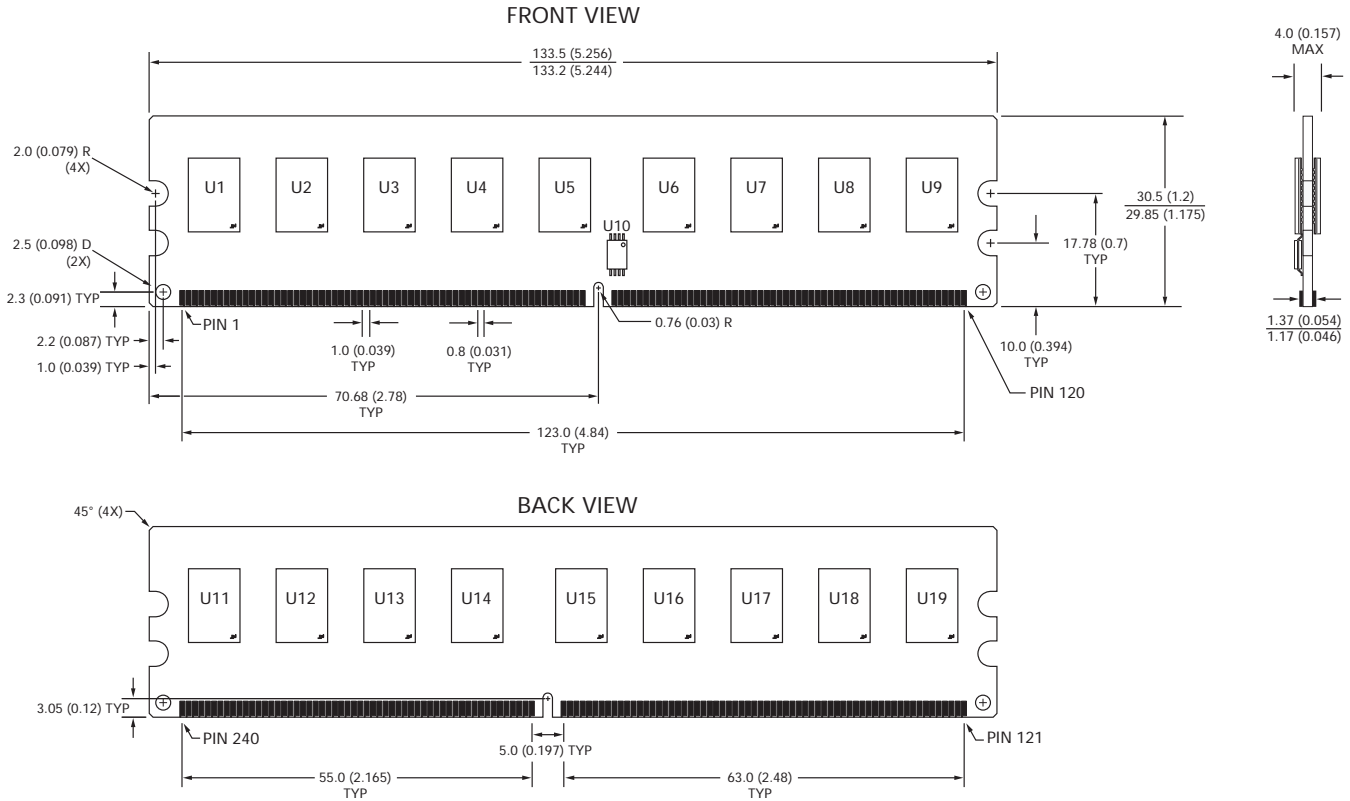
- Notes:
1. To avoid spurious start and stop conditions, a minimum delay is placed between SCL = 1 and the falling or rising edge of SDA.
 2. This parameter is sampled.
 3. For a restart condition or following a WRITE cycle.
 4. The SPD EEPROM WRITE cycle time (t_{WRC}) is the time from a valid STOP condition of a write sequence to the end of the EEPROM internal ERASE/PROGRAM cycle. During the WRITE cycle, the EEPROM bus interface circuit is disabled, SDA remains HIGH due to the pull-up resistor, and the EEPROM does not respond to its slave address.

Serial Presence-Detect Data

For the latest serial presence-detect data, refer to Micron's SPD page:
www.micron.com/SPD.

Module Dimensions

Figure 3: 240-Pin DDR2 DIMM



- Notes: 1. All dimensions are in millimeters (inches), MAX/MIN or typical (TYP) where noted.
2. The dimensional diagram is for reference only. Refer to the MO document for complete design dimensions.

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This data sheet contains minimum and maximum limits specified over the power supply and temperature range set forth herein. Although considered final, these specifications are subject to change, as further product development and data characterization sometimes occur.